

# **ESD Protection Diode**

# Ultra-Low Capacitance Micro-Packaged Diodes for ESD Protection ESD8472

The ESD8472 is designed to protect voltage sensitive components that require ultra-low capacitance from ESD and transient voltage events. Excellent clamping capability, low capacitance, high breakdown voltage, high linearity, low leakage, and fast response time make these parts ideal for ESD protection on designs where board space is at a premium. It has industry leading capacitance linearity over voltage making it ideal for RF applications. This capacitance linearity combined with the extremely small package and low insertion loss makes this part well suited for use in antenna line applications for wireless handsets and terminals.

#### **Features**

Industry Leading Capacitance Linearity Over Voltage

Ultra-Low Capacitance: 0.2 pFInsertion Loss: 0.030 dBm

• Small Footprint: 0.62 mm x 0.32 mm

Stand-off Voltage: 5.3 VLow Leakage: < 1 nA</li>

• Low Dynamic Resistance:  $< 1 \Omega$ 

• 1000 ESD IEC61000-4-2 Strikes ±8 kV Contact / Air Discharged

- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant

# **Typical Applications**

- RF Signal ESD Protection
- RF Switching, PA, and Antenna ESD Protection
- Near Field Communications
- USB 2.0, USB 3.0

## MAXIMUM RATINGS (T<sub>A</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
IEC 61000-4-2 Level 4 (Contact) (Note 1) IEC 61000-4-2 Level 4 (Air) (Note 1)	ESD	±20 ±20	kV
Maximum Peak Pulse Current IEC 61000-4-5 8/20 μs (Lightning) (Note 2)	I <sub>PP</sub>	2.4	Α
Total Power Dissipation (Note 3) @ T <sub>A</sub> = 25°C Thermal Resistance, Junction-to-Ambient	$P_{D} R_{ heta JA}$	300 400	mW °C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	–55 to +150	°C
Lead Solder Temperature - Maximum (10 Second Duration)	TL	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Non-repetitive current pulse at  $T_A = 25^{\circ}C$ , per IEC61000-4-2 waveform.
- 2. Non-repetitive current pulse at  $T_A = 25^{\circ}C$ , per IEC61000-4-5 waveform.

1

3. Mounted with recommended minimum pad size, DC board FR-4



# MARKING DIAGRAM



X3DFN2 CASE 152AF



4 = Specific Device Code

M = Date Code

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
ESD8472MUT5G	X3DFN2 (Pb-Free)	10000 / Tape & Reel
SZESD8472MUT5G	X3DFN2 (Pb-Free)	15000 / Tape & Reel

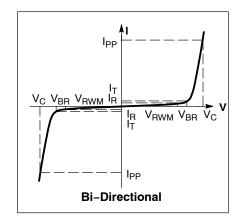
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# **ELECTRICAL CHARACTERISTICS**

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$ 

Symbol	Parameter
I <sub>PP</sub>	Maximum Reverse Peak Pulse Current
V <sub>C</sub>	Clamping Voltage @ I <sub>PP</sub>
V <sub>RWM</sub>	Working Peak Reverse Voltage
I <sub>R</sub>	Maximum Reverse Leakage Current @ V <sub>RWM</sub>
$V_{BR}$	Breakdown Voltage @ I <sub>T</sub>
I <sub>T</sub>	Test Current

<sup>\*</sup>See Application Note AND8308/D for detailed explanations of datasheet parameters.



# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Reverse Working Voltage	$V_{RWM}$				5.3	V
Breakdown Voltage	$V_{BR}$	I <sub>T</sub> = 1 mA (Note 4)	7.0		12	V
Reverse Leakage Current	I <sub>R</sub>	V <sub>RWM</sub> = 5.3 V		< 1	50	nA
Clamping Voltage	V <sub>C</sub>	I <sub>PP</sub> = 1 A (Note 5)		11	15	V
Clamping Voltage	V <sub>C</sub>	I <sub>PP</sub> = 2.4 A (Note 5)		15	17.8	V
ESD Clamping Voltage	V <sub>C</sub>	Per IEC61000-4-2	See Figures 1 and 2			
Junction Capacitance	CJ	$V_R = 0 \text{ V, } f = 1 \text{ MHz}$ $V_R = 0 \text{ V, } f = 1 \text{ GHz}$		0.20 0.15	0.30 0.30	pF
Dynamic Resistance	R <sub>DYN</sub>	TLP Pulse		0.75		Ω
Insertion Loss		f = 1 MHz f = 8.5 GHz		0.050 0.250		dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- 4. Breakdown voltage is tested from pin 1 to 2 and pin 2 to 1.
- 5. Non-repetitive current pulse at 25°C, per IEC61000-4-5 waveform (Figure 9).

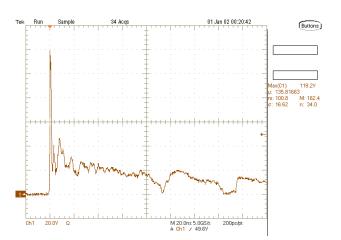


Figure 1. ESD Clamping Voltage Screenshot Positive 8 kV Contact per IEC61000-4-2

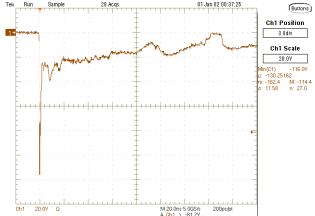


Figure 2. ESD Clamping Voltage Screenshot Negative 8 kV Contact per IEC61000-4-2

# **ESD8472**

# **TYPICAL CHARACTERISTICS**

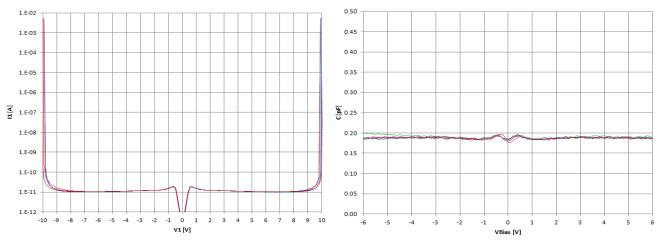


Figure 3. IV Characteristics

Figure 4. CV Characteristics

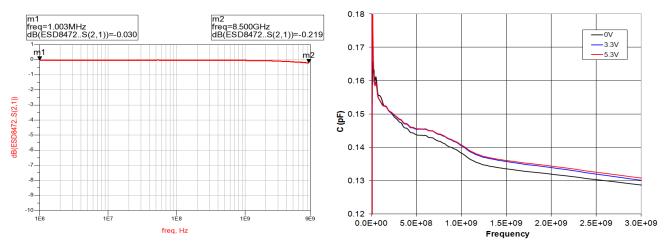


Figure 5. RF Insertion Loss

Figure 6. Capacitance over Frequency

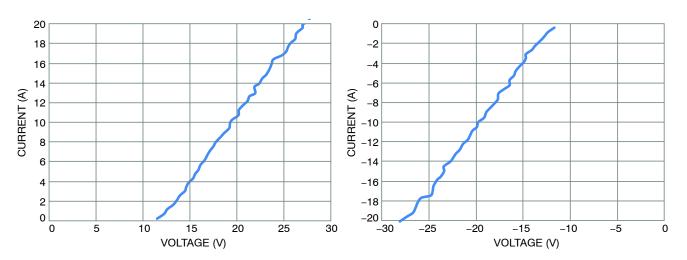


Figure 7. Positive TLP I-V Curve

Figure 8. Negative TLP I-V Curve

# ESD8472

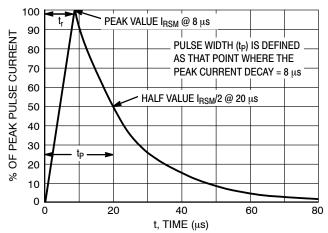


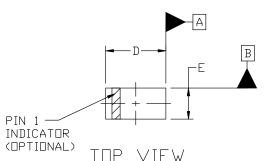
Figure 9. IEC 61000-4-5 8/20 μs Pulse Waveform

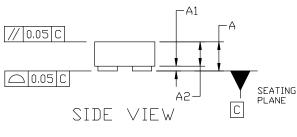


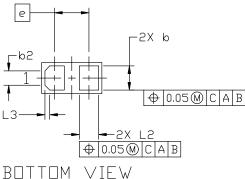


## X3DFN2 0.62x0.32x0.24, 0.35P CASE 152AF ISSUE C

**DATE 08 AUG 2023** 







# GENERIC MARKING DIAGRAM\*



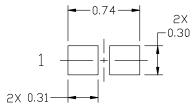
X = Specific Device Code

M = Date Code

#### NOTES:

- . DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. 0201

	MILLIMETERS		
DIM	MIN.	N□M.	MAX.
Α	0.25	0.29	0.33
A1	0.00		0.05
A2	0.14	0.24	0.34
b	0.22	0.25	0.28
b2	0.150 REF		
D	0.58	0.62	0.66
E	0.28	0.32	0.36
е	0.355 BSC		
L2	0.17	0.20	0.23
L3	0.050 REF		



RECOMMENDED
MOUNTING FOOTPRINT\*

For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98AON56472E	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	X3DFN2 0.62x0.32x0.24, 0.35P		PAGE 1 OF 1

onsemi and ONSemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

#### ADDITIONAL INFORMATION

**TECHNICAL PUBLICATIONS:** 

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$ 

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales